

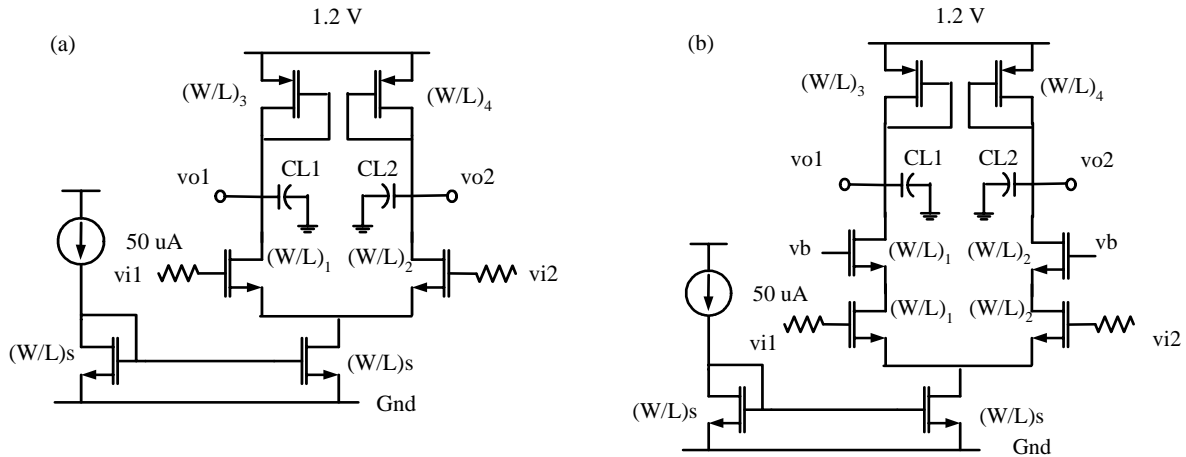
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**Homework #6**  
**(Due 4/06/04)**

**EECS 140**  
**Spring 2004**

- 1) Given the differential amplifier in figure 1, assuming  $(W/L)_3 = (W/L)_4 = 0.15\mu\text{m}/0.13\mu\text{m}$ ,  $(W/L)_1 = (W/L)_2 = 10\mu\text{m}/0.13\mu\text{m}$ ,  $(W/L)_s = 5\mu\text{m}/0.25\mu\text{m}$ ,  $V_{IC}=0.6\text{V}$ ,  $v_b=0.7\text{V}$ , input resistance =  $10\text{ k}\Omega$ , all bodies tied to  $V_{dd}/Gnd$ .
- Let  $CL1=CL2=0$ , find out the frequency response (poles and zeros) of differential mode gain,  $A_{dm}$ , in figure 1a.
  - Let  $CL1=CL2=1\text{ pF}$ , redo part (a).
  - Let  $CL1=CL2=0$ , find out the dominant pole (lowest frequency pole) of differential mode gain,  $A_{dm}$ , in figure 1b (cascoed amplifier). Explain the difference between part (c) and (a).
  - Verify (a)-(c) with SPICE. Explain any difference larger than 10%.



**Figure 1**

Device model:

```
.model nch nmos LEVEL=1 tox=2.6n vt0=0.3 gamma=0.2 phi=0.6 u0=250 ld=0.025u
+ capop=0 acm=3 ldif=0 hdif=0.2u cj=8e-4 cjsw=8e-12 cjgate=8e-11
+ lambda=0.2
.model pch pmos LEVEL=1 tox=2.6n vt0=-0.3 gamma=0.2 phi=0.6 u0=100 ld=0.025u
+ capop=0 acm=3 ldif=0 hdif=0.2u cj=8e-4 cjsw=8e-12 cjgate=8e-11
+ lambda=0.15
```

Spice Hint:

- AC analysis can plot the frequency response (Bode plot): `‘.ac dec 10 1 1T’`
- `.pz` can list the poles and zeros of the transfer function from input independent source `vin` to output node `v(out)`: `‘.pz v(out) vin’`

MOSFET capacitance calculation (saturation region):

Use the following formulas for the MOSFET capacitances to get your hand calculations to agree with Spice.

$$C_{gs} = 2/3 W (L-2LD)C_{ox} + W C_{gso} = 2/3 W (L-2LD)C_{ox} + W LD C_{ox}$$

$$C_{gd} = W C_{gdo} = W LD C_{ox}$$

$C_{ox}$  can be calculated from the Spice parameter  $tox$ .  $C_{ox} = \epsilon / tox = 3.453e-11/tox$

$LD$  is a Spice parameter.

$$C_{db} = \frac{C_j A_D}{\left(1 + \frac{V_{DB}}{PB}\right)^{m_j}} + \frac{C_{jsw} P_D + C_{jgate} W}{\left(1 + \frac{V_{DB}}{PB_{sw}}\right)^{m_{jsw}}}$$

$$A_D = W^2 HDIF$$

$$P_D = W + 4HDIF$$

$C_j$ ,  $C_{jsw}$ ,  $C_{jgate}$ ,  $PB$ ,  $m_j$  and  $HDIF$  are Spice paramers.

Default values:  $PB = PB_{sw} = 0.8V$ ,  $m_j = 1/2$ ,  $m_{jsw} = 1/3$ .

- 2) Given the RF amplifier shown in figure 2,
  - a) Consider only  $C_{gs}$  of the transistors. Derive frequency response of input impedance:  $Z_{in}(s)$  as a function of  $g_m$ , inductors and capacitors (including  $C_{gs}$ ) as denoted in figure 2.
  - b) Consider only  $C_{gs}$  of the transistors. The amplifier is designed to operate at 5 GHz. For the matching purpose, the input impedance has to be 50 ohm (purely real resistance). Calculate the value of  $L_2$ . Assume  $(W/L)=100\mu m/0.13\mu m$ , biasing current is 5 mA,  $K_n'=150 \mu A/V^2$ ,  $C_{ox}=0.015 F/m^2$ ,  $C_{gso}=C_{gdo}=5e-10 F/m$ ,  $\lambda=0$ . [Hint: The impedance of inductor is  $s*L$ ]

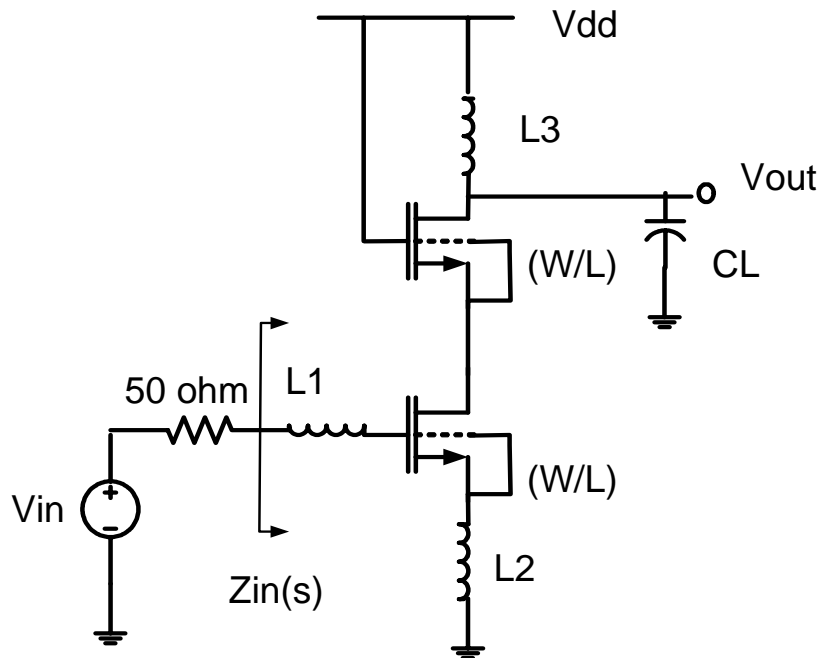


Figure 2